

2SK3372G

Silicon N-Channel Junction FET

For impedance conversion in low frequency

For electret capacitor microphone

■ Features

- High mutual conductance g_m
- Low noise voltage NV

■ Package

- Code
SSSMINI3-F2

• Pin Name

- 1: Drain
- 2: Source
- 3: Gate

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

| Parameter | Symbol | Rating | Unit |
|----------------------------------|-----------|-------------|------------------|
| Drain-source voltage (Gate open) | V_{DSO} | 20 | V |
| Gate-drain voltage (Source open) | V_{GDO} | 20 | V |
| Drain-source current (Gate open) | I_{DSO} | 2 | mA |
| Gate-drain current (Source open) | I_{GDO} | 2 | mA |
| Gate-source current (Drain open) | I_{GSO} | 2 | mA |
| Power dissipation | P_D | 100 | mW |
| Operating ambient temperature | T_{opr} | -20 to +80 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +125 | $^\circ\text{C}$ |

■ Marking Symbol: 1H

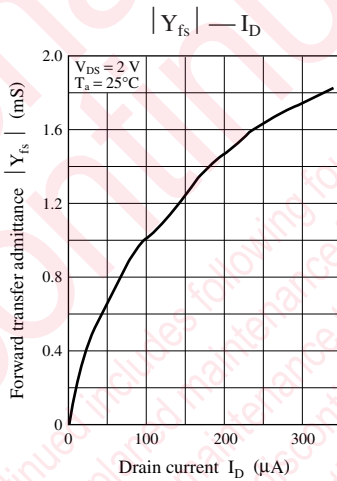
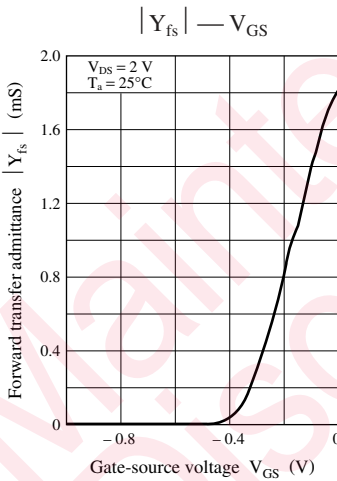
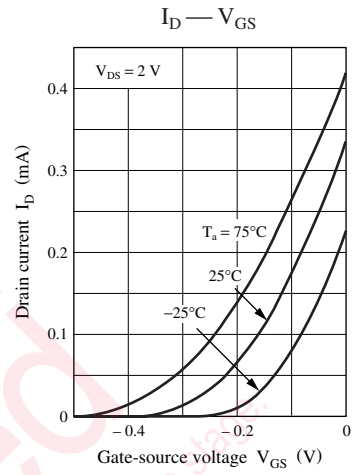
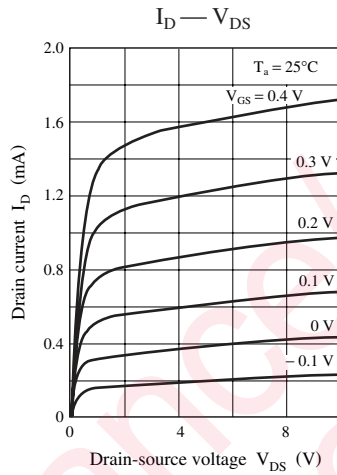
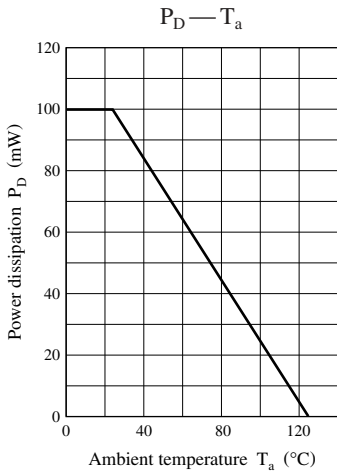
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|-------------------------|---------------------------|---|------|------|-----|---------------|
| Drain current *1 | I_D | $V_{DS} = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ | 100 | | 470 | μA |
| Drain-source current | I_{DSS} | $V_{DS} = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$, $V_{GS} = 0$ | 107 | | 460 | μA |
| Mutual conductance | g_m | $V_D = 2.0\text{ V}$, $V_{GS} = 0$, $f = 1\text{ kHz}$ | 660 | 1600 | | μS |
| Noise voltage | NV | $V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, A-Curve | | | 4 | μV |
| Voltage gain | G_{V1} | $V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$ | -7.5 | -4.7 | | dB |
| | G_{V2} | $V_D = 12\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$ | -4.0 | -1.5 | | |
| | G_{V3} | $V_D = 1.5\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$ | -8.0 | -5.0 | | |
| | $\Delta G_V \cdot f $ *2 | $V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz to } 70\text{ Hz}$ | | 0 | 1.7 | |
| Voltage gain difference | $ G_{V2} - G_{V1} $ | | 0 | | 4.0 | dB |
| | $ G_{V1} - G_{V3} $ | | 0 | | 1.7 | |

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

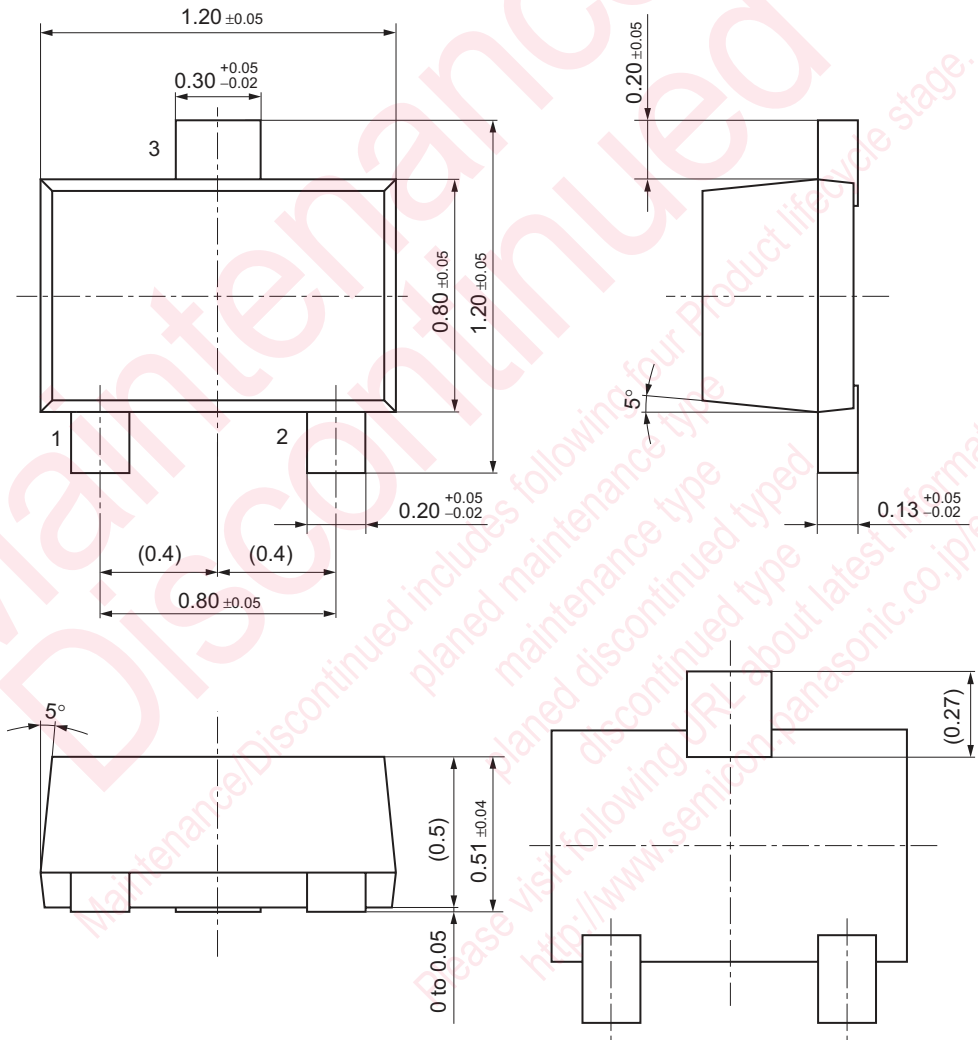
2. *1: I_D is assured for I_{DSS} .

*2: $\Delta |G_V \cdot f|$ is assured for AQL 0.065%. (The measurement method is used by source-grounded circuit.)



SSSMini3-F2

Unit: mm



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